

## OptiMOS™ Power-Transistor

### Features

- Optimized for high performance SMPS, e.g. sync. rec.
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21



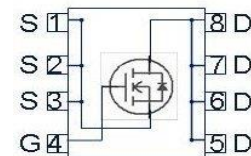
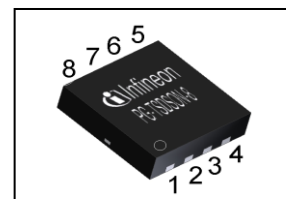
Halogen-Free



### Product Summary

|                  |    |    |
|------------------|----|----|
| $V_{DS}$         | 60 | V  |
| $R_{DS(on),max}$ | 10 | mΩ |
| $I_D$            | 40 | A  |
| $Q_{OSS}$        | 14 | nC |
| $Q_G(0V..10V)$   | 12 | nC |

PG-TSDSON-8  
(Fused Leads)



| Type        | Package                   | Marking |
|-------------|---------------------------|---------|
| BSZ100N06NS | PG-TSDSON-8 (Fused Leads) | 100N06N |

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                                    | Symbol        | Conditions                                                                   | Value | Unit |
|----------------------------------------------|---------------|------------------------------------------------------------------------------|-------|------|
| Continuous drain current                     | $I_D$         | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$                                    | 40    | A    |
|                                              |               | $V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$                                   | 29    |      |
|                                              |               | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$ ,<br>$R_{thJA}=60\text{ K/W}^{2)}$ | 11    |      |
| Pulsed drain current <sup>3)</sup>           | $I_{D,pulse}$ | $T_C=25\text{ °C}$                                                           | 160   |      |
| Avalanche energy, single pulse <sup>4)</sup> | $E_{AS}$      | $I_D=20\text{ A}$ , $R_{GS}=25\text{ Ω}$                                     | 19    | mJ   |
| Gate source voltage                          | $V_{GS}$      |                                                                              | ±20   | V    |

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See figure 3 for more detailed information

<sup>4)</sup> See figure 13 for more detailed information

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol                | Conditions                                                    | Value       | Unit |
|-------------------------------------|-----------------------|---------------------------------------------------------------|-------------|------|
| Power dissipation                   | $P_{\text{tot}}$      | $T_C=25\text{ °C}$                                            | 36          | W    |
|                                     |                       | $T_A=25\text{ °C}$ ,<br>$R_{\text{thJA}}=60\text{ K/W}^{(2)}$ | 2.1         |      |
| Operating and storage temperature   | $T_j, T_{\text{stg}}$ |                                                               | -55 ... 150 | °C   |
| IEC climatic category; DIN IEC 68-1 |                       |                                                               | 55/150/56   |      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Thermal characteristics

|                                     |                   |                                               |   |   |     |     |
|-------------------------------------|-------------------|-----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{\text{thJC}}$ | bottom                                        | - | - | 3.5 | K/W |
| Device on PCB                       | $R_{\text{thJA}}$ | 6 cm <sup>2</sup> cooling area <sup>(2)</sup> | - | - | 60  |     |

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

#### Static characteristics

|                                  |                             |                                                                                       |     |      |     |               |
|----------------------------------|-----------------------------|---------------------------------------------------------------------------------------|-----|------|-----|---------------|
| Drain-source breakdown voltage   | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}}=0\text{ V}$ , $I_{\text{D}}=1\text{ mA}$                               | 60  | -    | -   | V             |
| Gate threshold voltage           | $V_{\text{GS(th)}}$         | $V_{\text{DS}}=V_{\text{GS}}$ , $I_{\text{D}}=14\text{ }\mu\text{A}$                  | 2.1 | 2.8  | 3.3 |               |
| Zero gate voltage drain current  | $I_{\text{DSS}}$            | $V_{\text{DS}}=60\text{ V}$ , $V_{\text{GS}}=0\text{ V}$ ,<br>$T_j=25\text{ °C}$      | -   | 0.1  | 1   | $\mu\text{A}$ |
|                                  |                             | $V_{\text{DS}}=60\text{ V}$ , $V_{\text{GS}}=0\text{ V}$ ,<br>$T_j=125\text{ °C}$     | -   | 10   | 100 |               |
| Gate-source leakage current      | $I_{\text{GSS}}$            | $V_{\text{GS}}=20\text{ V}$ , $V_{\text{DS}}=0\text{ V}$                              | -   | 10   | 100 | nA            |
| Drain-source on-state resistance | $R_{\text{DS(on)}}$         | $V_{\text{GS}}=10\text{ V}$ , $I_{\text{D}}=20\text{ A}$                              | -   | 8.5  | 10  | mΩ            |
|                                  |                             | $V_{\text{GS}}=6\text{ V}$ , $I_{\text{D}}=5\text{ A}$                                | -   | 12.4 | 15  |               |
| Gate resistance                  | $R_{\text{G}}$              |                                                                                       | -   | 1.1  | 1.7 | Ω             |
| Transconductance                 | $g_{\text{fs}}$             | $ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}$ ,<br>$I_{\text{D}}=20\text{ A}$ | 16  | 33   | -   | S             |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

### Dynamic characteristics

|                              |              |                                                                                       |   |     |      |    |
|------------------------------|--------------|---------------------------------------------------------------------------------------|---|-----|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=30\text{ V},$<br>$f=1\text{ MHz}$                          | - | 860 | 1075 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                       | - | 210 | 263  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                       | - | 16  | 32   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=30\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=20\text{ A}, R_{G,ext}=1.6\ \Omega$ | - | 6   | -    | ns |
| Rise time                    | $t_r$        |                                                                                       | - | 2   | -    |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                       | - | 10  | -    |    |
| Fall time                    | $t_f$        |                                                                                       | - | 2   | -    |    |

### Gate Charge Characteristics<sup>5)</sup>

|                              |               |                                                                            |   |     |     |    |
|------------------------------|---------------|----------------------------------------------------------------------------|---|-----|-----|----|
| Gate to source charge        | $Q_{gs}$      | $V_{DD}=30\text{ V}, I_D=20\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 4.1 | -   | nC |
| Gate charge at threshold     | $Q_{g(th)}$   |                                                                            | - | 2.4 | -   |    |
| Gate to drain charge         | $Q_{gd}$      |                                                                            | - | 2.5 | 3.7 |    |
| Switching charge             | $Q_{sw}$      |                                                                            | - | 4.2 | -   |    |
| Gate charge total            | $Q_g$         |                                                                            | - | 12  | 15  |    |
| Gate plateau voltage         | $V_{plateau}$ |                                                                            | - | 4.8 | -   | V  |
| Gate charge total, sync. FET | $Q_{g(sync)}$ | $V_{DS}=0.1\text{ V},$<br>$V_{GS}=0\text{ to }10\text{ V}$                 | - | 10  | -   | nC |
| Output charge                | $Q_{oss}$     | $V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$                                    | - | 14  | -   |    |

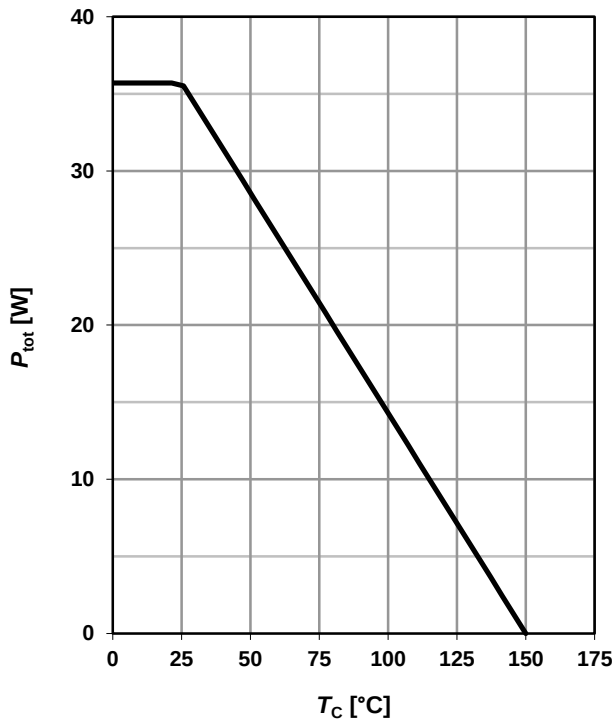
### Reverse Diode

|                                  |               |                                                                           |   |      |     |    |
|----------------------------------|---------------|---------------------------------------------------------------------------|---|------|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ °C}$                                                        | - | -    | 30  | A  |
| Diode pulse current              | $I_{S,pulse}$ |                                                                           | - | -    | 160 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=20\text{ A},$<br>$T_J=25\text{ °C}$               | - | 0.92 | 1.2 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=30\text{ V}, I_F=20\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 33   | 53  | ns |
| Reverse recovery charge          | $Q_{rr}$      |                                                                           | - | 30   | -   | nC |

<sup>5)</sup> See figure 16 for gate charge parameter definition

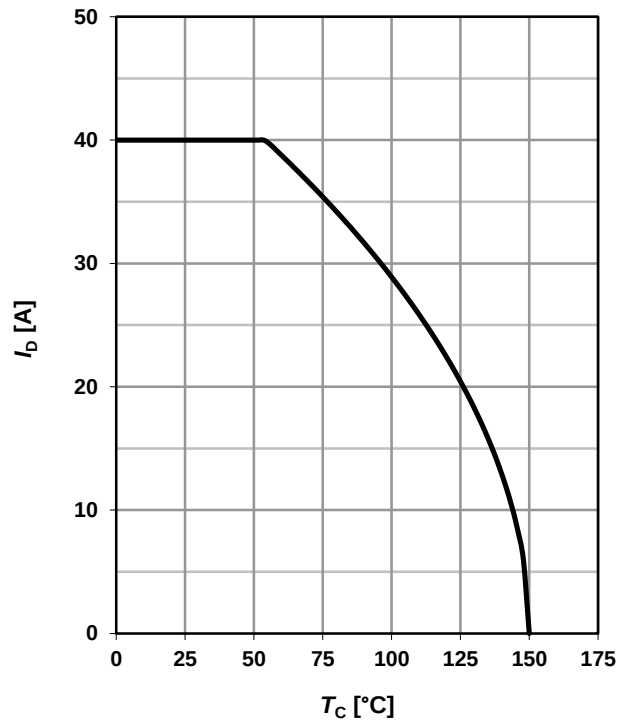
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



### 2 Drain current

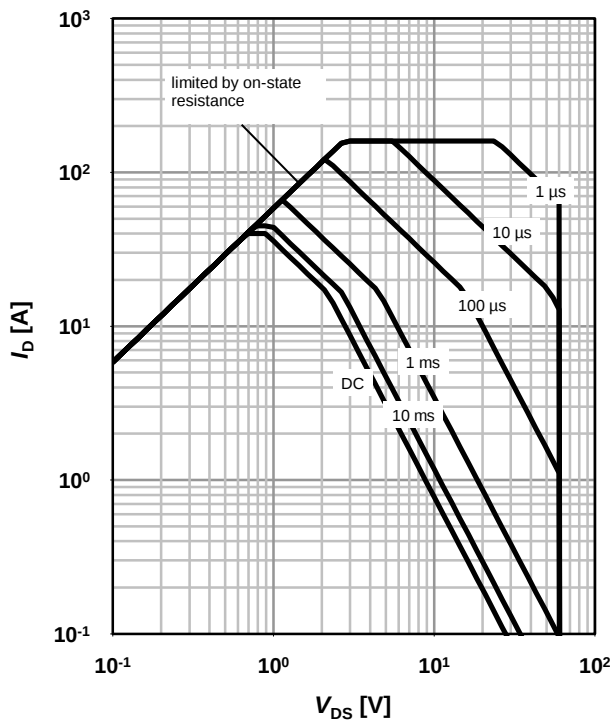
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

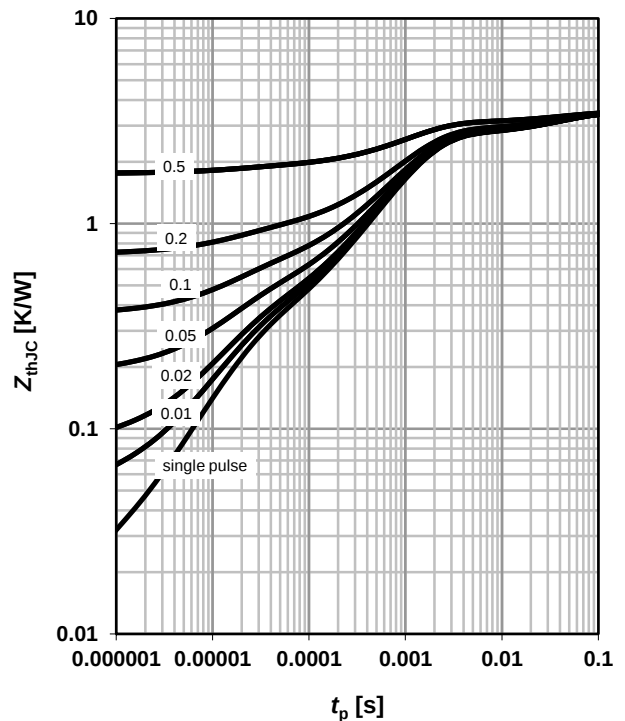
parameter:  $t_p$



### 4 Max. transient thermal impedance

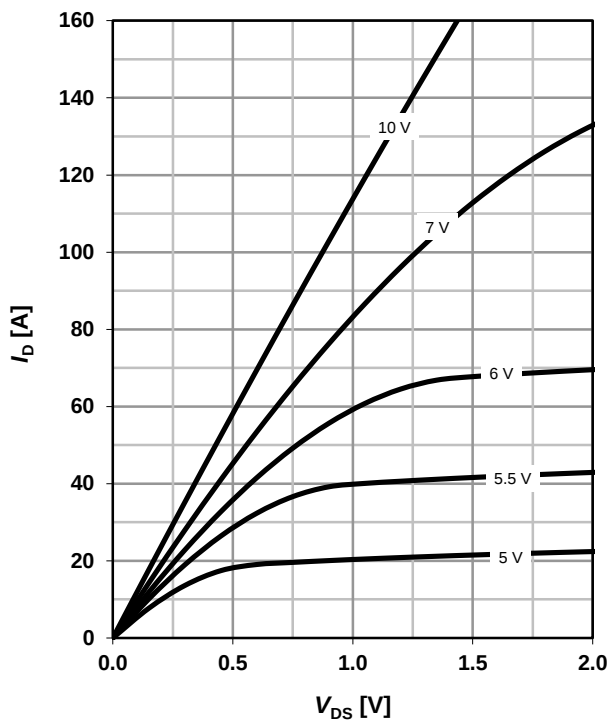
$$Z_{thJC} = f(t_p)$$

parameter:  $D = t_p / T$



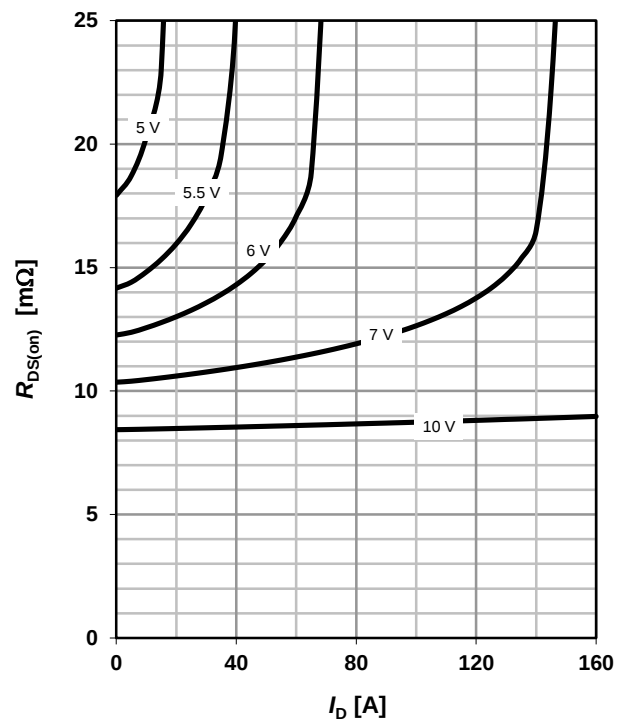
### 5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$ 

parameter:  $V_{GS}$ 


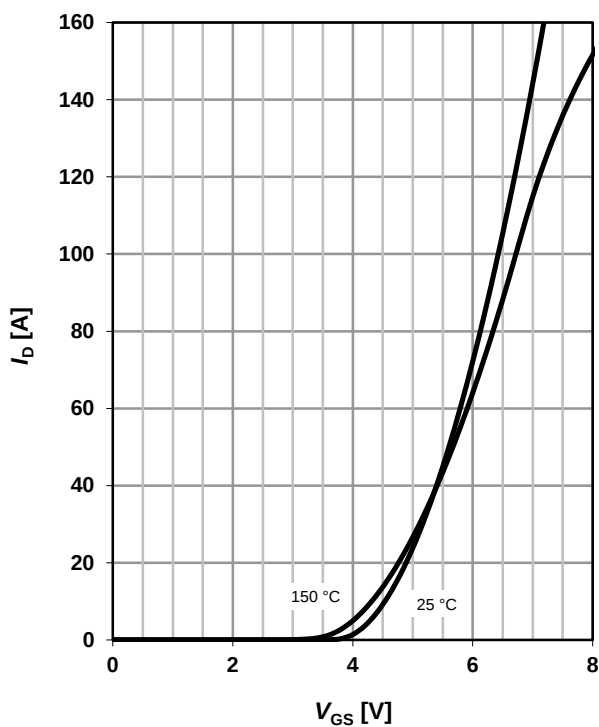
### 6 Typ. drain-source on resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$ 

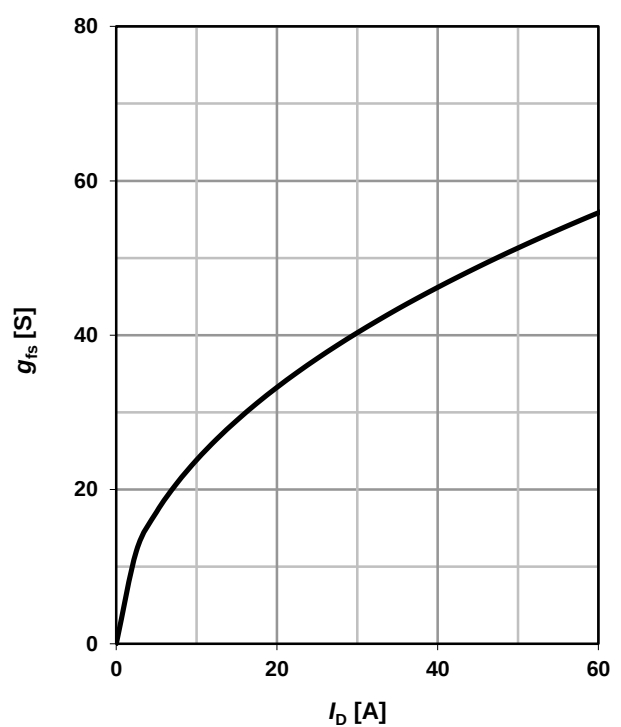
parameter:  $V_{GS}$ 


### 7 Typ. transfer characteristics

 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$ 

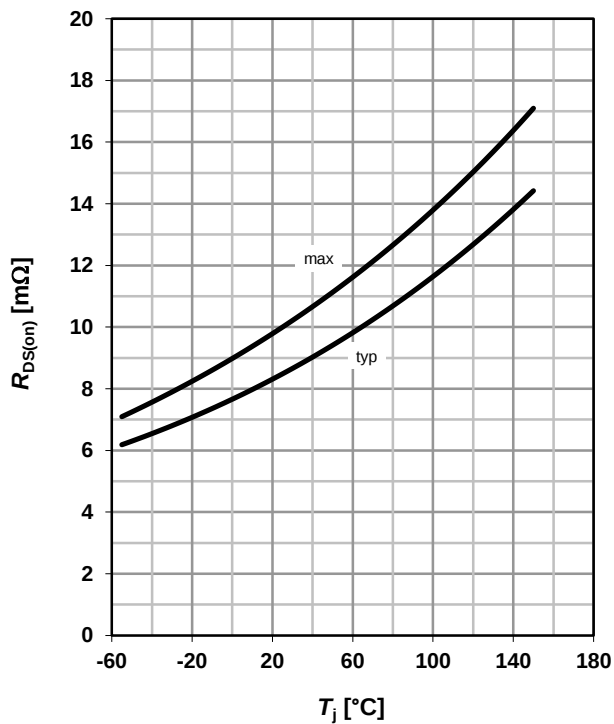
parameter:  $T_j$ 


### 8 Typ. forward transconductance

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$ 


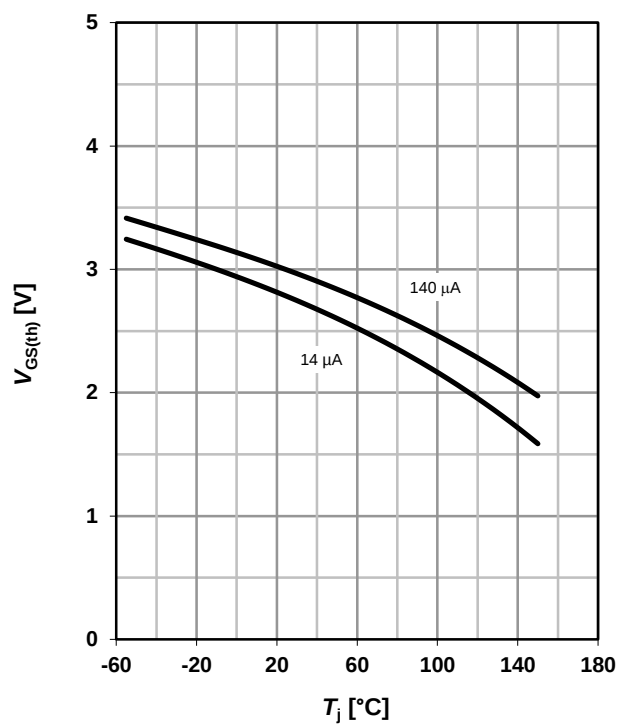
## 9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j); I_D = 20 \text{ A}; V_{GS} = 10 \text{ V}$$



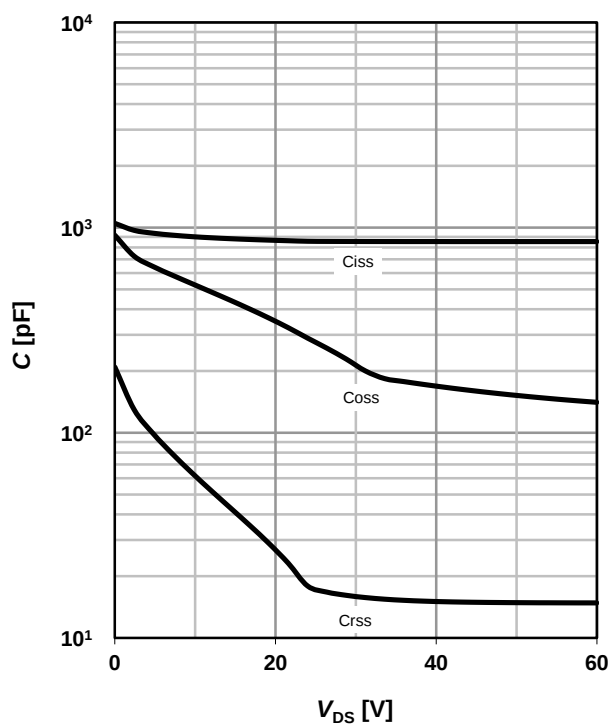
## 10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$



## 11 Typ. capacitances

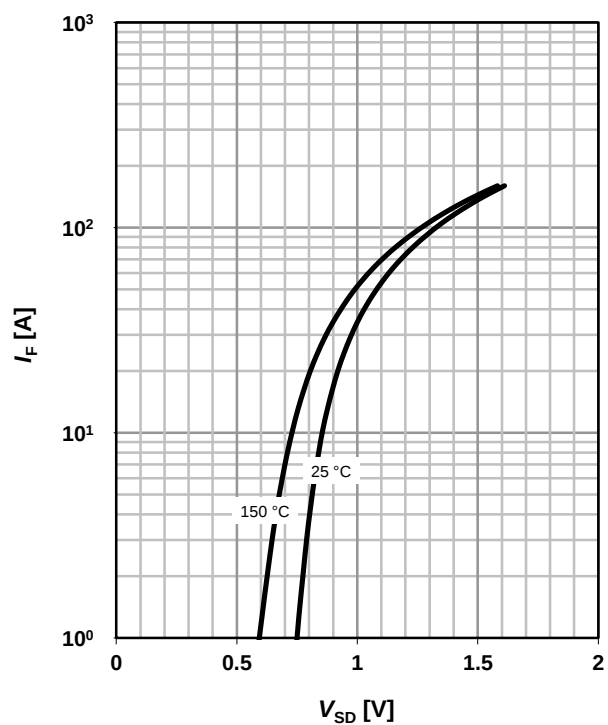
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



## 12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

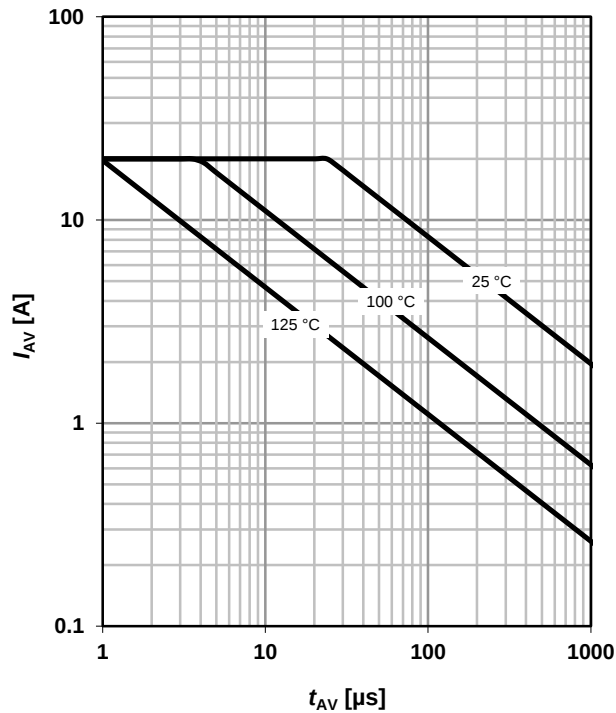
parameter:  $T_j$



### 13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

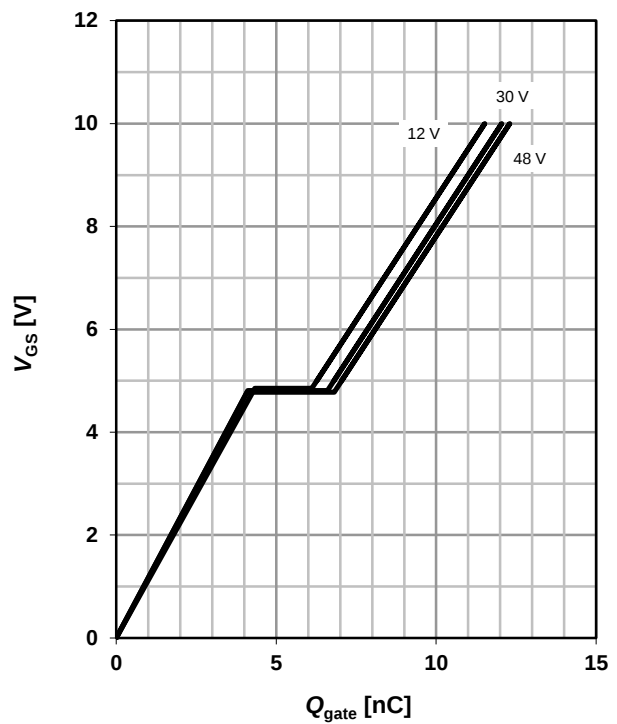
parameter:  $T_{j(\text{start})}$



### 14 Typ. gate charge

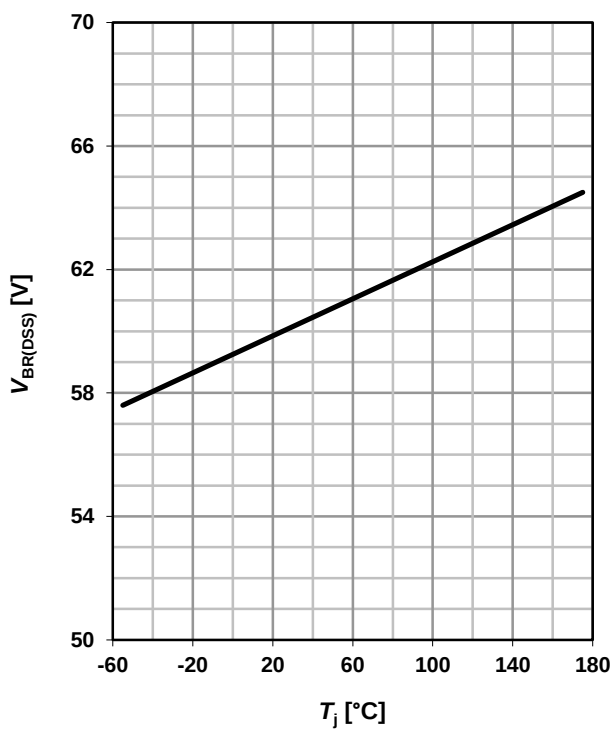
$$V_{GS}=f(Q_{\text{gate}}); I_D=20\ \text{A pulsed}$$

parameter:  $V_{DD}$



### 15 Drain-source breakdown voltage

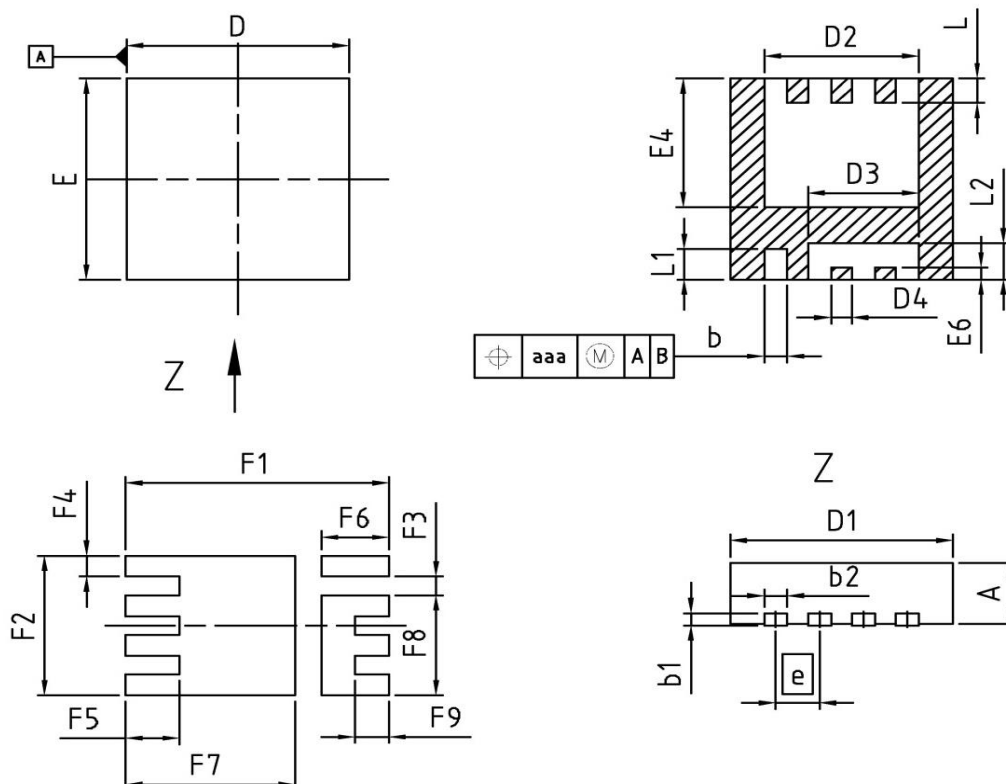
$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$



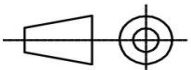
### 16 Gate charge waveforms



## PG-TSDSON-8 (Fused Leads): Outline



| DIM  | MILLIMETERS |      | INCHES      |       |
|------|-------------|------|-------------|-------|
|      | MIN         | MAX  | MIN         | MAX   |
| A    | 0.90        | 1.10 | 0.035       | 0.043 |
| b    | 0.24        | 0.44 | 0.009       | 0.017 |
| b1   | 0.10        | 0.30 | 0.004       | 0.012 |
| b2   | 0.24        | 0.44 | 0.009       | 0.017 |
| D=D1 | 3.20        | 3.40 | 0.126       | 0.134 |
| D2   | 2.19        | 2.39 | 0.086       | 0.094 |
| D3   | 1.54        | 1.74 | 0.061       | 0.069 |
| D4   | 0.21        | 0.41 | 0.008       | 0.016 |
| E    | 3.20        | 3.40 | 0.126       | 0.134 |
| E4   | 2.01        | 2.21 | 0.079       | 0.087 |
| E6   | 0.10        | 0.30 | 0.004       | 0.012 |
| e    | 0.65 (BSC)  |      | 0.026 (BSC) |       |
| N    | 8           |      | 8           |       |
| L    | 0.30        | 0.51 | 0.012       | 0.020 |
| L1   | 0.40        | 0.70 | 0.016       | 0.028 |
| L2   | 0.50        | 0.70 | 0.020       | 0.028 |
| aaa  | 0.25        |      | 0.010       |       |
| F1   | 3.90        |      | 0.154       |       |
| F2   | 2.29        |      | 0.090       |       |
| F3   | 0.31        |      | 0.012       |       |
| F4   | 0.34        |      | 0.013       |       |
| F5   | 0.80        |      | 0.031       |       |
| F6   | 1.00        |      | 0.039       |       |
| F7   | 2.51        |      | 0.099       |       |
| F8   | 1.64        |      | 0.065       |       |
| F9   | 0.50        |      | 0.020       |       |

|                                                                                                                     |
|---------------------------------------------------------------------------------------------------------------------|
| <b>DOCUMENT NO.</b><br>Z8B00158553                                                                                  |
| <b>SCALE</b><br>0 2.5 5mm                                                                                           |
| <b>EUROPEAN PROJECTION</b><br> |
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